

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

2SK3051

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
 Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 24 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 27 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 50 \text{ V}$)
- Enhancement-Mode : $V_{th} = 1.5 \sim 3.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	50	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	50	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	45	A
	Pulse	I_{DP}	135	A
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)		P_D	40	W
Single Pulse Avalanche Energy**		E_{AS}	115	mJ
Avalanche Current		I_{AR}	45	A
Repetitive Avalanche Energy*		E_{AR}	4	mJ
Channel Temperature		T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

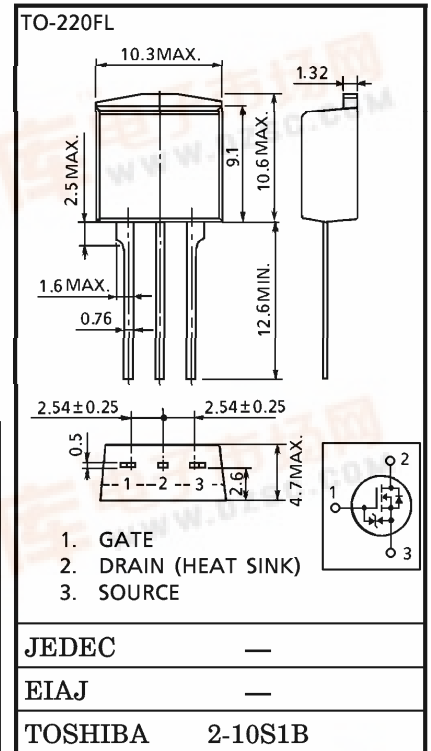
THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ\text{C}/\text{W}$

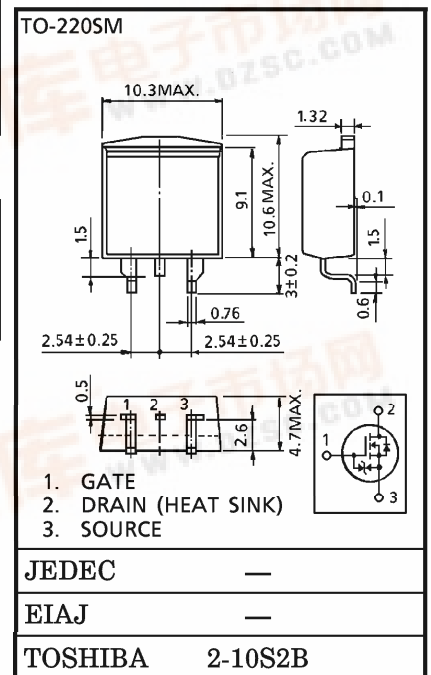
Note ;

- * Repetitive rating ; Pulse Width Limited by Max. junction temperature.
- ** $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 71 \mu\text{H}$, $R_G = 25 \Omega$, $I_{AR} = 45 \text{ A}$

This transistor is an electrostatic sensitive device.
 Please handle with caution.



Weight : 1.5 g (Typ.)



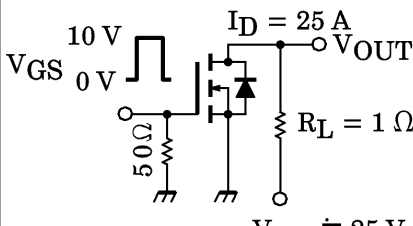
Weight : 1.5 g (Typ.)

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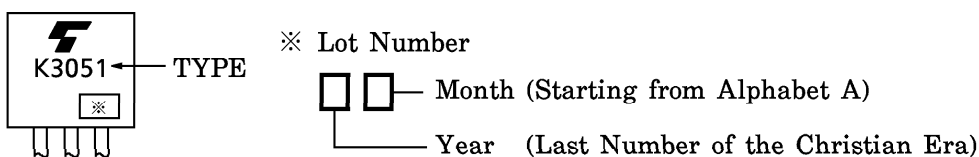
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	50	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$	—	24	30	$\text{m}\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	15	27	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	1250	—	pF
Reverse Transfer Capacitance		C_{rss}		—	250	—	
Output Capacitance		C_{oss}		—	700	—	
Switching Time	Rise Time	t_r	 <p>$I_D = 25\text{ A}$ $V_{GS} = 10\text{ V}, 0\text{ V}$ $R_L = 1\ \Omega$ $V_{DD} \doteq 25\text{ V}$ $V_{IN} : t_r, t_f < 5\text{ ns},$ $\text{Duty} \leq 1\%, t_w = 10\ \mu\text{s}$</p>	—	20	—	ns
	Turn-on Time	t_{on}		—	30	—	
	Fall Time	t_f		—	40	—	
	Turn-off Time	t_{off}		—	120	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 40\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 45\text{ A}$	—	36	—	nC
Gate-Source Charge		Q_{gs}		—	22	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	14	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	45	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	135	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	75	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	75	—	nC

MARKING



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